## JAYPEE UNIVERSITY OF INFORMATION TECHNOLOGY, WAKNAGHAT MAKEUP EXAMINATION- 2016

## B.Tech, II Semester

COURSE CODE: 10B11EC211

MAX. MARKS: 25

COURSE NAME: BEDC SAME AND A COURSE OF SAME AND A C

COURSE CREDITS: 04 (1) (1) (1) (1) (1)

MAX. TIME: 1Hr 30 Min

Note: All questions are compulsory. Carrying of mobile phone during examinations will be treated as case of unfair means.

Q.1.	Determine the intrinsic carrier concentration of germanium if its intrinsic resistivity at 300 K is $0.47\Omega m$ .	02
	Given that the electron and hole mobilities are 0.39 m <sup>2</sup> /Vs and 0.19 m <sup>2</sup> /Vs, respectively.	
Q.2.	A half-wave rectifier circuit uses a silicon diode with $r_{\rm f}=10~\Omega$ and $V_{\rm T}=0.7$ V. The load connected at the output is $R_{\rm L}=500~\Omega$ . The transformer has $N_1/N_2=10/1$ . If the primary is connected to the ac mains supply (220 V, 50 Hz), calculate  (a) the dc current through the load, (b) the rectification efficiency, and (c) the PIV rating of the diode.	03
Q.3.	A PNP transistor with $\beta$ = 200 is used in the circuit of Fig 1. A dc supply of 9 V and $R_{\rm C}$ of 1.5 k $\Omega$ are	04
	used. The operating point is to be fixed at $I_c = 2$ rnA. Calculate the value of $R_B$ and the voltage $V_{CE}$ .	
	Fig.1 $V_{cc}$ $R_1$ $R_2$ $R_2$ $R_E$	
Q.4	For the Fig2. Calculate the collector current and the collector-to-emitter voltage. Make necessary	05
	assumptions to simplify calculations.( Use approximate method)	j.
	$R_{\rm C} = 5 \text{ k}\Omega$ $R_{\rm I} = 40 \text{ k}\Omega$ $V_{\rm CC} = 12 \text{ V}$	

